

1SS184

PRV : 85 Volts
I_o : 100 mA

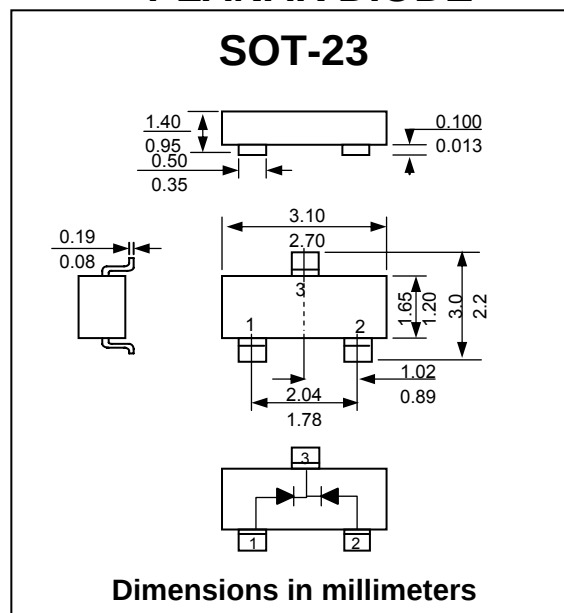
FEATURES :

- * Small package
- * Low forward voltage
- * Fast reverse recovery time
- * Small total capacitance
- * Ultra high speed switching application
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : SOT-23 plastic Case
- * Marking Code : B3

SILICON EPITAXIAL PLANAR DIODE



MAXIMUM RATINGS AND THERMAL CHARACTERISTICS (Ta =25 °C)

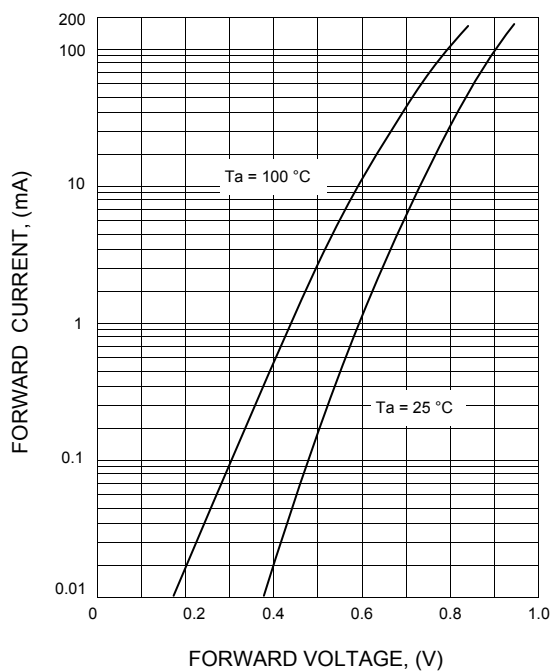
Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	80	V
Maximum Peak Forward Current	I _{FM}	300	mA
Average Forward Current	I _{F(AV)}	100	mA
Surge Current (10 ms)	I _{FSM}	2	A
Power Dissipation	P _{tot}	150	mW
Junction Temperature	T _J	125	°C
Storage Temperature Range	T _{STG}	-55 to +125	°C

ELECTRICAL CHARACTERISTICS (Ta =25 °C)

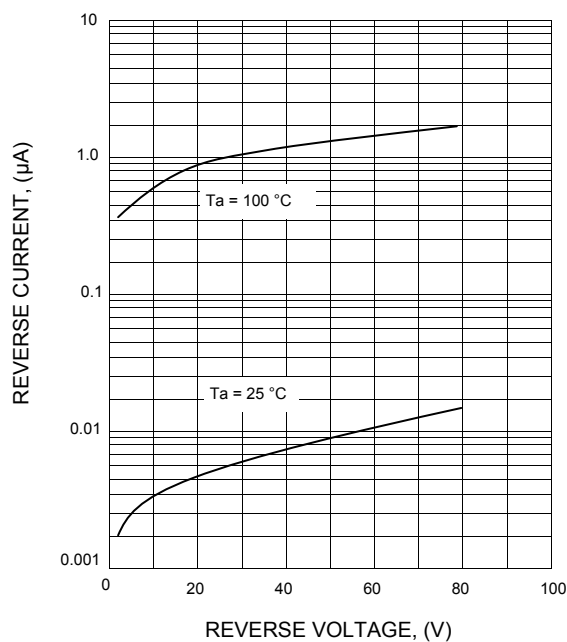
Parameter	Test Condition	Symbol	Min.	TYP	Max.	Unit
Forward Voltage	I _F = 1 mA	V _F	-	0.6	-	V
	I _F = 10 mA		-	0.72	-	
	I _F = 100 mA		-	0.9	1.2	
Reverse Current	V _R = 30 V	I _R	-	-	0.1	μA
	V _R = 80 V		-	-	0.5	
Total Capacitance	V _R = 0 V, f = 1 MHz	C _T	-	0.9	3	pF
Reverse Recovery Time	I _R = 10 mA	T _{rr}	-	1.6	4	ns

RATINGS AND CHARACTERISTIC CURVES (1SS184)

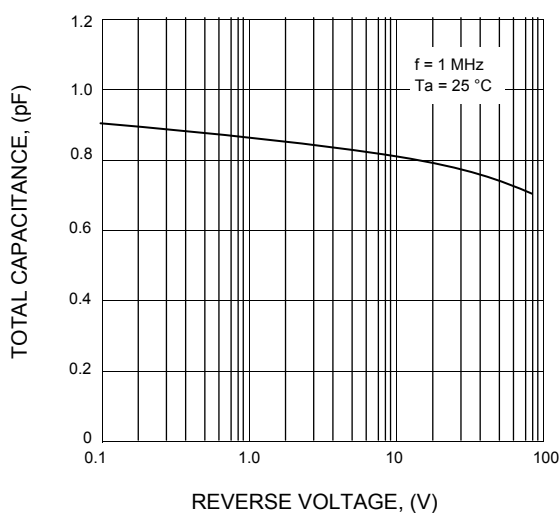
**FIG.1 - FORWARD CURRENT VS.
FORWARD VOLTAGE**



**FIG.2 - REVERSE CURRENT VS.
REVERSE VOLTAGE**



**FIG.3 - TOTAL CAPACITANCE VS.
REVERSE VOLTAGE**



**FIG.4 - REVERSE RECOVERY TIME VS.
FORWARD CURRENT**

